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Abstract Title for the 3rd Japan-China Academic Symposium on Nuclear Fuel Cycle
(**Bold, 12 point, Times or Times New Roman**)

First Author^a, Second Author^b, Third Author^{b,*}

(11point, Times or Times New Roman, Name of the presenting author is underlined.)

^a *Affiliation 1*

^b *Affiliation 2*

(*Italic, 11point, Times or Times New Roman*)

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This page presents instructions for preparing abstracts for the 3rd Japan-China Academic Symposium on Nuclear Fuel Cycle (ASNFC 2015).

The abstracts will be printed in 2 page of A4-size and the set of instructions is given in the style and format to be used by the authors. For A4-size, set all margins to 25mm. (If you use US letter size, set all margins to 1 inch.)

The title should be placed at the top, followed by the author(s) name(s), affiliation(s) and address(es), and email address of the contact person. Use capital letters for the initial letter of each word except articles, prepositions and conjunctions. Place a blank line between the title and author name(s), and between address(es) and the main text. **The main text** should be typed by using 11 point Times (or Times New Roman) font with 14-pt line spacing. References should be placed at the end of the main text with a blank line before the reference.

The length must be **one full page or two pages including figures and tables**. If your manuscript includes digital photographs, the resolution should be at least 150dpi. Figure captions should be placed below the figures; table captions above the tables. Arabic numbers should be used for the figures like Fig.1, and Roman numbers for tables like Table I. Place a blank line between the text and the tables or figures. Font style is 12pt bold for the title, 11pt italic for affiliations and addresses, and 11pt normal for others. List and number all the references at the end of the paper as below. The reference number should be designed like [1], [2,3] and [4,7-9] when referring to them in the text.

[1] A. Bcde, F. Ghijk, L. Mnop, Q. Rstu and V. Wxyz, Appl. Phys. Lett. xx, 2067 (2006).

[2] Z. Yxwv, U.Tsrq, P. Onml, K. Jihg and E. Dcba, J. Crystal Growth xx, yyy (2007)

[3] S. Sze, Physics of Semiconductor Devices, (Academic Press, New York, 1978), Part B, p.15.

Table I. Topics of Workshop

No.	Thematic
1.	III-nitride compounds
2.	Optical properties
3.	Nanostructures
4.	Organic semiconductors
5.	Electronic devices

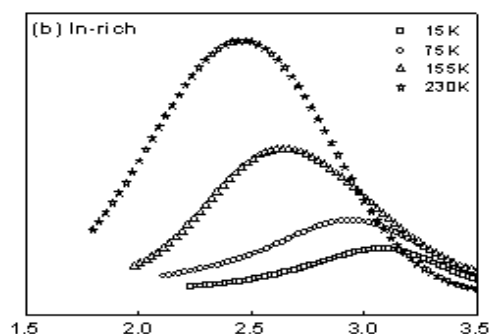


Fig. 1. The building for meeting proceeding.
(printed in grey scale in the abstract)